Silicon PNP Power Transistors 2SA887

DESCRIPTION
·With TO-202 package
·Complement to type 2SC1848

APPLICATIONS
·Medium power amplifier

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

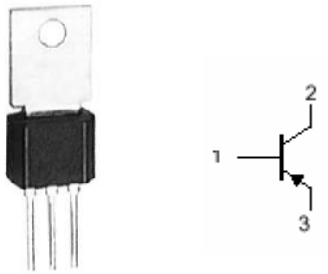

Fig.1 simplified outline (TO-202) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-70	V
V_{CEO}	Collector-emitter voltage	Open base	-50	V
V_{EBO}	Emitter-base voltage	Open collector	-5	V
I_C	Collector current		-2	A
I_{CM}	Collector current-peak		-3	A
P_C	Collector power dissipation	T_a=25□	1.2	W
		T_C=25□	10	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA; I_B=0	-50			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-1mA; I_E=0	-70			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-1A ;I_B=-0.1A		-0.6	-1.2	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-2A ;I_B=-0.2 A		-1.0	-1.5	V
h_{FE-1}	DC current gain	I_C=-100mA ; V_{CE}=-5V	30			
h_{FE-2}	DC current gain	I_C=-1A ; V_{CE}=-5V	50		220	
I_{CBO}	Collector cut-off current	V_{CB}=-40V; I_E=0			-1.0	μA
I_{CEO}	Collector cut-off current	V_{CE}=-20V; I_B=0			-100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-10	μA
f_T	Transition frequency	I_E=0.5A ; V_{CB}=-5V		150		MHz

◆ **h_{FE-2} Classifications**

P	Q	R
50-100	80-160	120-220

PACKAGE OUTLINE

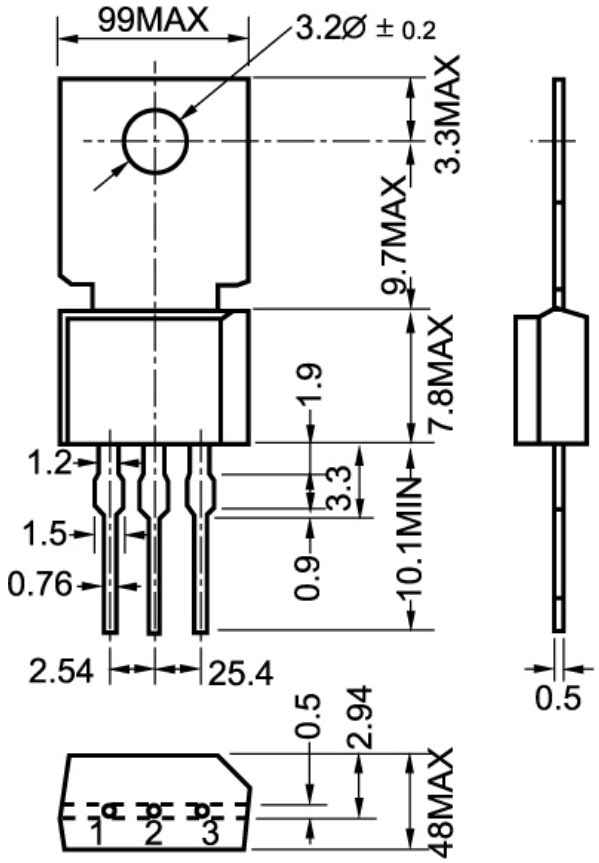

Fig.2 outline dimensions